

BLE Module

DATASHEET

Description

The ATBTLC1000-MR110CA is an ultra-low power Bluetooth® SMART (BLE 4.1) module with Integrated Transceiver, Modem, MAC, PA, TR Switch, and Power Management Unit (PMU). It can be used as a Bluetooth Low Energy link controller or data pump with external host MCU.

The qualified Bluetooth® Smart protocol stack is stored in dedicated ROM, the firmware includes L2CAP service layer protocols, Security Manager, Attribute protocol (ATT), Generic Attribute Profile (GATT), and the Generic Access Profile (GAP). Additionally, application profiles such as Proximity, Thermometer, Heart Rate, Blood Pressure and many others are supported and included in the protocol stack.

The module contains all circuitry required including a ceramic high gain antenna, 26MHz crystal, and PMU circuitry. The customer simply needs to place the module on his board and provide power and a 32KHz Real Time Clock or crystal.

Features

- Complies with Bluetooth V4.1, ETSI EN 300 328, and EN 300 440 Class 2, FCC CFR47 Part 15, ARIB STD-T66, and TELEC
- Bluetooth Certification
 - QD ID Controller (see declaration D028678)
 - QD ID Host (see declaration D028679)
- 2.4GHz transceiver and Modem
 - 95dBm/-93dBm programmable receiver sensitivity
 - -20 to +3.5dBm programmable TX output power
 - Integrated T/R switch
 - Single wire antenna connection
- ARM Cortex®-M0 32-bit processor
 - Single wire Debug (SWD) interface
 - 4-channel DMA controller
 - Brown out detector and Power On Reset
 - Watch Dog Timer
- Memory
 - 128kB embedded RAM (96kB available for application)
 - 128kB embedded ROM
- Hardware Security Accelerators
 - AES-128
 - SHA-256



Peripherals

- 12 digital and 1 wake-up GPIO
- Two Mixed Signal GPIOs
- Programmable 96kΩ pull-up or pull-down resistor for each GPIO
- Retention capable GPIO pads
- 1x SPI (Master/Slave)
- 2x I²C (Master/Slave)
- 2x UART
- 1x SPI Flash
- 3-axis quadrature decoder
- 4x Pulse Width Modulation (PWM), three General Purpose Timers, and one Wake up Timer
- 2-channel 11-bit ADC

Clock

- Integrated 26MHz oscillator
- 26MHz crystal oscillator
- Fully integrated sleep oscillator
- 32kHz RTC crystal oscillator

Ultra Low power

- Less than 1.15µA (8KB RAM retention and RTC running)
- 3.0mA peak TX current (VBAT=3.6V, 0dBm TX power)
- 4.2mA peak RX current (VBAT=3.6V, -95dBm sensitivity)
- Very low average advertisement current (dependent on advertisement interval)

Integrated Power management

- 1.8-4.3V input range for PMU
- 1.62-4.3V input range for I/O
- Fully integrated Buck DC-DC converter



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1 Ordering Information

Ordering code	Package	Description		
ATBTLC1000-MR110CA	12.7 X 20.15mm	Chip Antenna		

2 Package Information

Table 2-1. ATBTLC1000-MR110 Module Information (1)

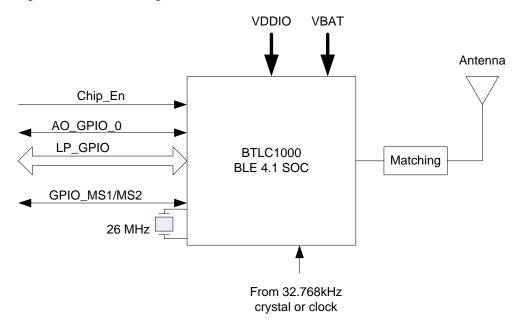
Parameter	Value	Units	Tolerance
Package Size	12.700 X 20.152	mm	
Pad Count	24		
Total Thickness	2.0874	mm	
Pad Pitch	.9002		
Pad Width	.500		
Exposed Pad size	2.7 x 2.7		

Note: 1. For details, see Package Drawing in Section 4.3.

3 Block Diagram

Figure 3-1 shows the block diagram of the ATBTLC1000-MR110CA module.

Figure 3-1. Block Diagram



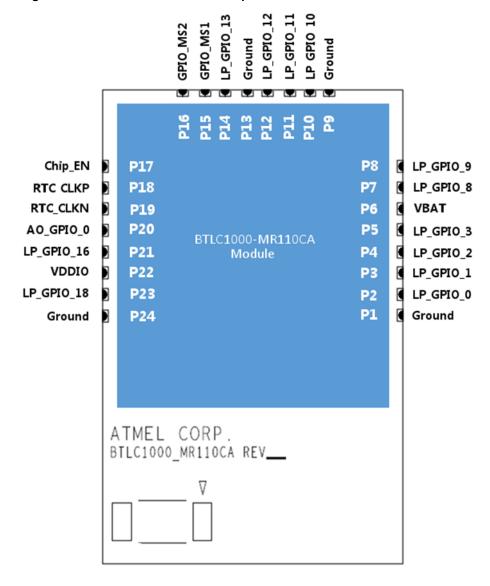


4 Pin-out Information

4.1 Pin Assignment

Figure 4-1 shows the module top view and pin numbering.

Figure 4-1. ATBTLC1000 Pin Descriptions



4.2 **Pin Description**

Table 4-1 provides details for the module pin assignments and descriptions.

Table 4-1. **Pin Description**

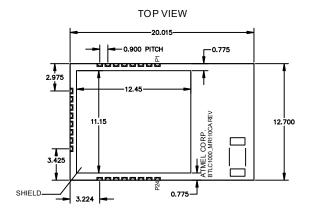
NO	Name	Туре	Description	Notes
1	Ground	Power	Ground Pin. Connect to PCB ground.	
2	LP_GPIO_0	I/O	Used for Single Wire Debug Clock	Debug interface pin. Connect to a header or test point.
3	LP_GPIO_1	I/O	Used for Single Wire Debug Data	Debug interface pin. Connect to a header or test point
4	LP_GPIO_2	I/O	General Purpose I/O	Default function is Host UART RxD
5	LP_GPIO_3	I/O	General Purpose I/O	Default function is Host UART TxD
6	VBAT	Power	Power Supply Pin for the on chip Power Management Unit (PMU). Connect to a 1.8V – 4.3V power supply.	
7	LP_GPIO_8	I/O	General Purpose I/O	Default function is Host UART CTS
8	LP_GPIO_9	I/O	General Purpose I/O	Default function is Host UART RTS
9	Ground	Power	Ground Pin. Connect to PCB ground.	
10	LP_GPIO_10	I/O	General Purpose I/O	Default function is SPI_SCK
11	LP_GPIO_11	I/O	General Purpose I/O	Default function is SPI_MOSI
12	LP_GPIO_12	I/O	General Purpose I/O	Default function is SPI_SSN
13	Ground	Power	Ground Pin. Connect to PCB ground.	
14	LP_GPIO_13	I/O	General Purpose I/O	Default function is SPI_MISO
15	GPIO_MS1	I/O	Mixed Signal I/O	Configurable to be a GPIO or ADC input
16	GPIO_MS2	I/O	Mixed Signal I/O	Configurable to be a GPIO or ADC input
17	Chip_En	Control	Chip Enable. A high level turns on the On Chip PMU and enables operation of the device. Low disables the device and turns off the PMU.	Control this pin with a host GPIO. If not used, tie to VDDIO.
18	RTC_CLKP		Positive Pin for Real Time Clock Crystal	Connect to a 32.768KHz Crystal
19	RTC_CLKN		Negative Pin for Real Time Clock Crystal	Connect to a 32.768KHz Crystal
20	AO_GPIO_0	I/O	Always on GPIO_0. Used to wake up the device from sleep.	
21	LP_GPIO_16	I/O	General Purpose I/O	Default function is Debug UART RxD
22	VDDIO	Power	Power Supply Pin for the I/O pins. Connect to a 1.62V – 4.3V power supply.	I/O supply can be less than or equal to VBAT
23	LP_GPIO_18	I/O	General Purpose I/O.	Default function is Debug UART TxD
24	Ground	Power	Ground Pin. Connect to PCB ground	
25	Paddle	Power	Center Ground Paddle	Connect to inner PCB ground plane with an array of vias

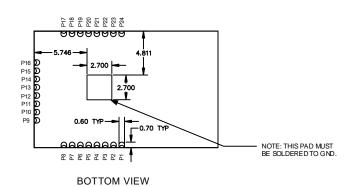


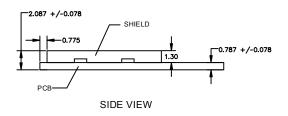
4.3 Module Outline Drawing

Figure 4-2 shows the view of the module and the module dimensions. All dimensions are in mm.

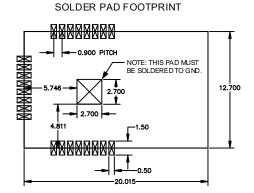
Figure 4-2. Module Dimensions (millimeters)







TOP VIEW



ATMEL BTLC1000-MR110CA

Electrical Specifications 5

5.1 **Absolute Maximum Ratings**

This section describes the minimum and maximum ratings the module can tolerate.

Table 5-1. ATBTLC1000-MR110CA Absolute Maximum Ratings

Symbol	Characteristics	Min.	Max.	Unit
VDDIO	I/O Supply Voltage	-0.3	4.6	V
VBAT	Battery Supply Voltage	-0.3	5.0	V
VIN (1)	Digital Input Voltage	-0.3	VDDIO	V
VAIN (2)	Analog Input Voltage	-0.3	1.5	V
VESDHBM (3)	ESD Human Body Model	-1000, -2000 (see notes below)	+1000, +2000 (see notes below)	V
TA	Storage Temperature	-65	150	°C
	Junction Temperature		125	°C

- Notes: 1. VIN corresponds to all the digital pins.
 - VAIN corresponds to the following analog pins: VDDRF_RX, VDDAMS, RFIO, XO_N, XO_P, VDD_SXDIG, VDD VCO.
 - 3. For VESDHBM, each pin is classified as Class 1, or Class 2, or both:
 - The Class 1 pins include all the pins (both analog and digital)
 - The Class 2 pins include all digital pins only
 - VESDHBM is ±1kV for Class1 pins. VESDHBM is ±2kV for Class2 pins.

5.2 **Recommended Operating Conditions**

Table 5-2. ATBTLC1000-MR110CA Recommended Operating Conditions

Symbol	Characteristics	Min.	Тур.	Max.	Unit
VDDIO	I/O Supply Voltage Low Range	1.62	1.80	4.3	V
VBAT	Battery Supply Voltage	1.8 (1)	3.6	4.3	V
	Operating Temperature	-40		85	°C

Note: 1. VBAT supply must be greater than or equal to VDDIO.

5.3 **Restrictions for Power States**

When VDDIO is off (either disconnected or at ground potential), a voltage must not be applied to the device pins. This is because each pin contains an ESD diode from the pin to the VDDIO supply. This diode will turn ON when a voltage higher than one diode-drop is supplied to the pin. This in turn will try to power up the part through the VDDIO supply.

If a voltage must be applied to the signal pads while the chip is in a low power state, the VDDIO supply must be on.

Similarly, to prevent the pin-to-ground diode from turning on, do not apply a voltage that is more than 0.3V below ground to any pin.



5.4 Power Sequences

Describes that sequence and parameters for powering up and down the device.

5.4.1 Power-up Sequence

The power-up sequence for ATBTLC1000 is shown in Figure 5-1. The timing parameters are provided in Table 5-3.

Figure 5-1. ATBTLC1000 Power-up Sequence

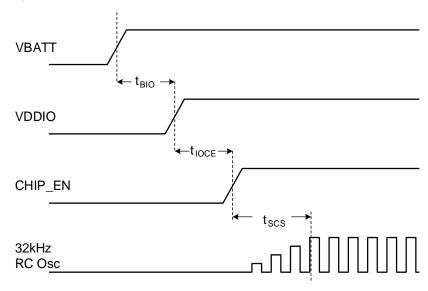


Table 5-3. ATBTLC1000 Power-up Sequence Timing

Parameter	Min.	Max.	Unit	Description	Notes
t _{BIO}	0			VBATT rise to VDDIO rise	VBATT and VDDIO can rise simultaneously or can be tied together.
tioce	0		Ms	VDDIO rise to CHIP_EN rise	CHIP_EN must not rise before VDDIO. CHIP_EN must be driven high or low, not left floating.
t _{SCS}	10		μs	CHIP_EN rise to 31.25kHz (2MHz/64) oscillator stabilizing	

5.4.2 **Power-down Sequence**

The power-down sequence for ATBTLC1000 is shown in Figure 5-2. The timing parameters are provided in Table 5-5.

Figure 5-2. ATBTLC1000 Power-down Sequence

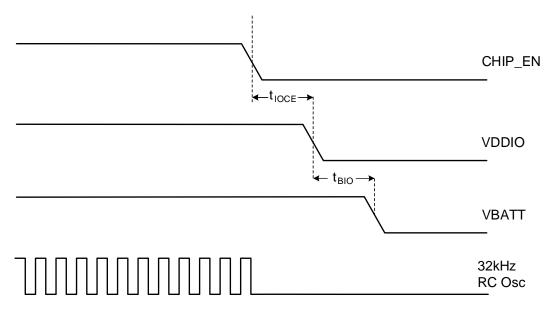


Table 5-4. ATBTLC1000 Power-down Sequence Timing

Parameter	Min.	Max.	Unit	Description	Notes
tioce	0		ms	CHIP_EN fall to VDDIO fall	CHIP_EN must fall before VDDIO. CHIP_EN must be driven high or low, not left floating
tBIO	0			VDDIO fall to VBATT fall	VBATT and VDDIO can fall simultaneously or can be tied together

Digital I/O Pin Behavior During Power-up Sequences 5.5

Table 5-5 describes the digital I/O Pin states corresponding to device power modes.

Table 5-5. Digital I/O Pin Behavior in Different Device States

Device state	VDDIO	CHIP_EN	RESETN	Output driver	Input driver	Pull-up/down resistor (96kΩ)
Power_Down: core supply off	High	Low	Low	Disabled (Hi-Z)	Disabled	Disabled
Power-On Reset: core supply on	High	High	Low	Disabled (Hi-Z)	Disabled	Enabled
Power-On Default: core sup- ply on, device out of reset but not programmed yet	High	High	High	Disabled (Hi-Z)	Enabled	Enabled
Power-On Default: core sup- ply on, device out of reset but not programmed yet	High	High	High	Programmed by firmware for each pin: Enabled or Disabled	Opposite of Output Driver state	Programmed by firmware for each pin: Ena- bled or Disabled



5.6 RTC Pins

Module pins 18 and 19 (RTC_CLKP and RTC_CLKN, respectively) are used for a 32.768KHz crystal. To be compliant with the BLE specifications for connection events, the frequency accuracy of this clock has to be within ±500ppm. Because of the low drift of the 32.768kHz crystal oscillator clock and the fact that it can be accurately calibrated (±25ppm), the power consumption of the ATBTLC1000 can be minimized by leaving radio circuits in low power sleep mode for as long as possible until they need to wake up for the next connection timed event.

The block diagram in Figure 5-3(a) shows how the internal low frequency Crystal Oscillator (XO) is connected to the external crystal.

Typically, the crystal should be chosen to have a load capacitance of 7pF to minimize the oscillator current.

Alternatively, if an external 32.768KHz clock is available, it can be used to drive the RTC_CLKP pin instead of using a crystal. The XO has 6pF internal capacitance on the RTC_CLKP pin. To bypass the crystal oscillator an external signal capable of driving 6pF can be applied to the RTC_CLK_P terminal as shown in Figure 5-3(b). This signal must be 1.2V maximum. RTC_CLK_N must be left unconnected when driving an external source into RTC_CLK_P.

Figure 5-3. ATBTLC1000 Connections to Low Frequency Crystal Oscillator

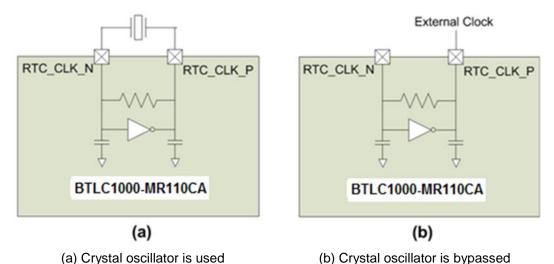


Table 5-6. ATBTLC1000-MR110CA 32.768KHz External Clock Specification

Parameter	Min.	Тур.	Max	Unit	Comments
Oscillation frequency		32.768		KHz	Must be able to drive 6pF load @ desired frequency
VinH	0.7		1.2	V	High level input voltage
VinL	0		0.2	V	Low level input voltage
Stability – Temperature	-250		+250	ppm	

Characteristics 6

6.1 **Device States**

Table 6-1. ATBTLC1000-MR110CA Device States

Device state	CHIP_EN	VDDIO	IVBAT (typical)	IVDDIO (typical)	Remarks
BLE_On_Transmit	On	On	3.0mA	0.0μΑ	VBAT = 3.6V @ 0dBm Pout
BLE_On_Receive	On	On	4.2mA	0.0μΑ	VBAT = 3.6V
Ultra Low Power	On	On	1.25µA	0.0μΑ	With 8KB retention memory, BLE Timer and RTC enabled
Power_Down	GND	On	<0.05µA	<0.05µA	Chip Enable Off

6.2 **Receiver Performance**

Table 6-2. ATBTLC1000-MR110CA Receiver Performance

Parameter	Min.	Тур.	Max.	Unit
Frequency	2,402		2,480	MHz
Sensitivity (max. RX Gain setting)		-95		dBm
Maximum Receive Signal Level		0		dBm
CCI		13		dB
ACI (N±1)		0		dB
N+2 Blocker (Image)		-20		dB
N-2 Blocker		-30		dB
N+3 Blocker (Adj. Image)		-32		dB
N-3 Blocker		-44		dB
N±4 or greater	-45			dB
Intermod (N+3, N+6)		-33		dBm
OOB (2GHz <f<2.399ghz)< td=""><td></td><td>-15</td><td></td><td>dBm</td></f<2.399ghz)<>		-15		dBm
OOB (f<2GHz)		-10		dBm

Note: Expected values for production silicon.

All measurements performed at 3.6V VBAT and 25°C, with tests following Bluetooth V4.1 standard tests.



6.3 Transmitter Performance

Table 6-3. ATBTLC1000-MR110CA Transmitter Performance

Parameter	Min.	Тур.	Max.	Unit
Frequency	2,402		2,480	MHz
Output Power Range	-20		3.5	dBm
Minimum Output Power	-55			
In-band Spurious (N±2)		-40		dBm
In-band Spurious (N±3)		-50		dBm
2nd Harmonic Pout		-45		dBm
Frequency Dev		250		kHz

All measurements performed at 3.6V VBAT and 25°C, with tests following Bluetooth V4.1 standard tests.

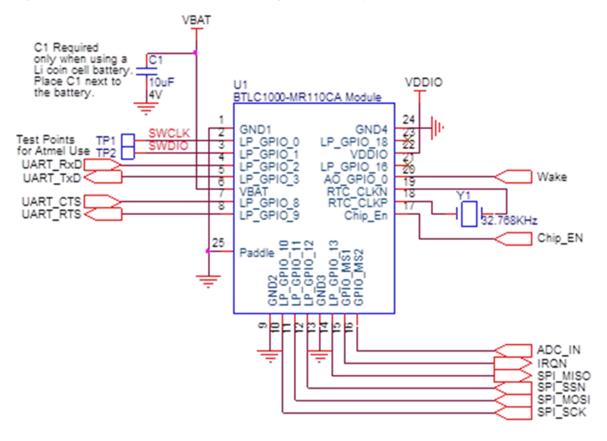
7 **Schematic Content**

This chapter provides the schematic data for the ATBTLC1000 chip functionality on the ATBTLC1000-MR210 module. Module design information such as module schematics can be obtained under a NDA from Atmel.

7.1 **Application Schematic**

The ATBTLC1000-MR110 module is fully self-contained. To use the module, just provide VBAT and VDDIO supplies. Figure 7-1 shows a typical design using the ATBTLC1000-MR110 module. The schematic shows several host interfaces: UART with Flow Control (4-wire) and SPI as well as an input to the ADC on the GPIO MS2 pin. A user can choose the interface(s) required for their application. If a 32.768KHz Real Time Clock is not available in the system, a 32.768KHz crystal can be used. Figure 7-2 shows a design using a crystal for the Real Time Clock. The crystal should be specified with a load capacitance, CL=7pF and a total frequency error of 200ppm.

Figure 7-1. Application Schematic Including 32.768KHz Crystal





VBAT C1 Required only when using a Li coin cell battery. Place C1 next to 10uF **VDDIO** the battery. 4V BTLC1000-MR110CA Module 24 GND4 LP_GPIO_18 VDDIO GND1 23 22 SWCLK 2 LP_GPIO_0 LP_GPIO_1 LP_GPIO_2 LP_GPIO_3 VBAT LP_GPIO_9 Test Points TP1 for Atmel Use TP2 SWDIO 3 20 19 18 LP_GPIO_18 AO_GPIO_0 RTC_CLKN RTC_CLKP Chip_En UART_RxD 5 UART_TxD Wake ő UART_CTS UART_RTS < 32.768 kHz 17 8 Chip_EN GND2 = GND2 = CND2 = CND2 = CND2 = CND2 = CND3 = CND3 = CND3 = CND3 = CND3 = CND3 = CND2 = CN 25 Paddle - Z Z Z Z 2 თ**_** ADC_IN IRQN SPI_MISO SPI_SSN SPI_MOSI SPI_SCK

Figure 7-2. Application Schematic without 32.768KHz Crystal



8 **Placement and Routing Guidelines**

It is critical to follow the recommendations listed below to achieve the best RF performance:

- The board should have a solid ground plane. The center ground pad of the device must be solidly connected to the ground plane by using a 3 x 3 grid of vias. Each ground pin of the module should have a ground via placed either in the pad or right next to the pad going down to the ground plane.
- When the module is placed on the motherboard, a provision for the antenna must be made. There should be nothing under the portion of the module, which contains the antenna. This means the antenna should not be placed directly on top of the motherboard PCB. This can be accomplished by, for example, placing the module at the edge of the board such that the module edge with the antenna extends beyond the main board edge by 6.5mm. Alternatively, a cutout in the motherboard can be provided under the antenna. The cutout should be at least 22mm x 6.5mm. Ground vias spaced 2.5mm apart should be placed all around the perimeter of the cutout. No large components should be placed near the antenna.
- Keep away from antenna, as far as possible, large metal objects to avoid electromagnetic field blocking
- Do not enclose the antenna within a metal shield
- Keep any components which may radiate noise or signals within the 2.4GHz 2.5GHz frequency band far away from the antenna or better yet, shield those components. Any noise radiated from the main board in this frequency band will degrade the sensitivity of the module.

8.1 **Power and Ground**

Dedicate one layer as a ground plane. Make sure that this ground plane does not get broken up by routes. Power can route on all layers except the ground layer. Power supply routes should be heavy copper fill planes to insure the lowest possible inductance. The power pins of the module should have a via directly to the power plane as close to the pin as possible. Decoupling capacitors should have a via right next to the capacitor pin and this via should go directly down to the power plane – that is to say, the capacitor should not route to the power plane through a long trace. The ground side of the decoupling capacitor should have a via right next to the pad which goes directly down to the ground plane. Each decoupling capacitor should have its own via directly to the ground plane and directly to the power plane right next to the pad. The decoupling capacitors should be placed as close to the pin that it is filtering as possible.



9 Interferers

One of the biggest problems with RF receivers is poor performance due to interferers on the board radiating noise into the antenna or coupling into the RF traces going to input LNA. Care must be taken to make sure that there is no noisy circuitry placed anywhere near the antenna or the RF traces. All noise generating circuits should also be shielded so they do not radiate noise that is picked up by the antenna. Also, make sure that no traces route underneath the RF portion of the ATBTLC1000. Also, make sure that no traces route underneath any of the RF traces from the antenna to the ATBTLC1000 input. This applies to all layers. Even if there is a ground plane on a layer between the RF route and another signal, the ground return current will flow on the ground plane and couple into the RF traces.



10 **Reference Documentation and Support**

10.1 **Reference Documents**

Atmel offers a set of collateral documentation to ease integration and device ramp.

The following list of documents available on Atmel web or integrated into development tools.

Title	Content
Datasheet	This document
ATBTLC1000 SOC Datasheet	Data sheet for the ATBTLC1000 SOC contained on this module.
SW Design Guide	Integration guide with clear description of: High level Arch, overview on how to write a networking application, list all API, parameters and structures. Features of the device, SPI/handshake protocol between device and host MCU, with flow/sequence/state diagram, timing.
SW Programmer guide	Explain in details the flow chart and how to use each API to implement all generic use cases (e.g. start AP, start STA, provisioning, UDP, TCP, http, TLS, p2p, errors management, connection/transfer recovery mechanism/state diagram) - usage and sample application note



11 Certifications

11.1 Agency Compliance

The ATBTLC1000-MR110CA has been tested and certified to meet the compliance for the following agencies:

- Bluetooth 4.1
 - QD ID Controller (see declaration D028678)
 - QD ID Host (see declaration D028679)
- FCC
 - FCC ID: 2ADHKBTLC1000
- CFR47 Part 15
- ETSI
 - EN 300 328
 - EN 300 400 Class 2
- ARIB
 - STD-T66
- TELEC

Reflow Profile Information 12

This chapter provides guidelines for reflow processes in getting the Atmel module soldered to the customer's design.

12.1 **Storage Condition**

12.1.1 Moisture Barrier Bag Before Opened

A moisture barrier bag must be stored in a temperature of less than 30°C with humidity under 85% RH.

The calculated shelf life for the dry-packed product shall be 12 months from the date the bag is sealed.

12.1.2 Moisture Barrier Bag Open

Humidity indicator cards must be blue, <30%.

12.2 Stencil Design

The recommended stencil is laser-cut, stainless-steel type with thickness of 100µm to 130µm, and approximately a 1:1 ratio of stencil opening to pad dimension. To improve paste release, a positive taper with bottom opening 25µm larger than the top can be utilized. Local manufacturing experience may find other combinations of stencil thickness and aperture size to get good results.

12.3 **Baking Conditions**

This module is rated at MSL level 3. After the sealed bag is opened, no baking is required within 168 hours so long as the devices are held at ≤30°C/60% RH or stored at <10% RH.

The module will require baking before mounting if:

- The sealed bag has been open for >168 hours
- Humidity Indicator Card reads >10%
- SIPs need to be baked for 8 hours at 125°C

Soldering and Reflow Condition 12.4

12.4.1 Reflow Oven

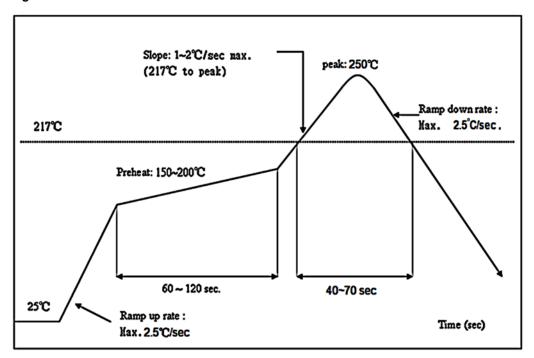
It is strongly recommended that a reflow oven equipped with more heating zones and Nitrogen atmosphere be used for lead-free assembly. Nitrogen atmosphere has shown to improve the wet-ability and reduce temperature gradient across the board. It can also enhance the appearance of the solder joints by reducing the effects of oxidation.

The following bullet items should also be observed in the reflow process:

- Some recommended pastes include NC-SMQ[®] 230 flux and Indalloy[®] 241 solder paste made up of 95.5 Sn/3.8 Ag/0.7 Cu or SENJU N705-GRN3360-K2-V Type 3, no clean paste.
- Allowable reflow soldering times: Three times based on the following reflow soldering profile (see Figure 12-
- Temperature profile: Reflow soldering shall be done according to the following temperature profile (see Figure 12-1).
- Peak temp: 250°C.



Figure 12-1. Solder Reflow Profile



13 Errata

Issue: The measured current for the device state cases listed in Table 6-1 will be higher than what is reported in the table.

This is because the Power number values in the SDK4.0 release have not been fully optimized to their final values.

A small sample measurement has been performed on 10 samples and they show the following results:

Measurement condition:

- 1-sec adverting interval
- 37 byte advertising payload
- Connectable beacon
- Advertising on three channels (37, 38, and 39)
- Vbatt and VDDIO are set to 3.3V

SAM L21 has a measurement floor of 80nA which was compensated in the reported numbers (this number varies from board to board and needs to be compensated).

The Average advertising current: 11.3µA

The Average sleep current between beacons: 1.17µA

The average current for the 10 boards was (including 80nA floor):

Sample #	1	2	3	4	5	6	7	8	9	10
Average Current (μA)	11.55	11.45	11.45	11.7	11.4	11.25	10.95	11.2	11.6	11.4

Work around: Will be resolved in a SDK update.

For a complete listing of development-support tools and documentation, visit http://www.atmel.com/ or contact the nearest Atmel field representative.



14 Revision History

Doc Rev.	Date	Comments	
42514D	03/2106	 Corrected package table ground pad size in Table 2-1. Updated module drawing in Figure 4-2. Corrected Errata to refer to Table 6-1. Revised reflow recurrence in Section 13. 	
42514C	12/2015	 Updated performance numbers. Added UART Flow Control. Added clearer diagrams. Added Agency Certification section. Corrected Package size value in Order information Chapter 1. Updated Module Drawing figure in Section 4.3. Revised Schematic content Chapter 7. Added Reflow Profile Chapter 12. Added Errata Chapter 13. 	
42514B	07/2015	Updated for B0 silicon	
42514A	04/2015	Initial release	















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